

FIG. 1

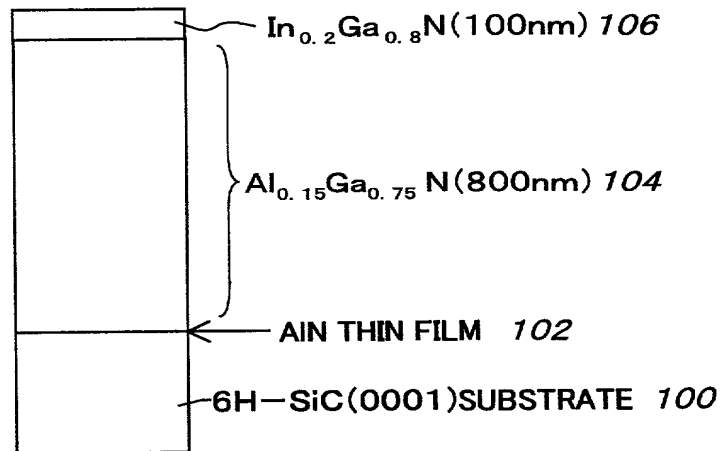
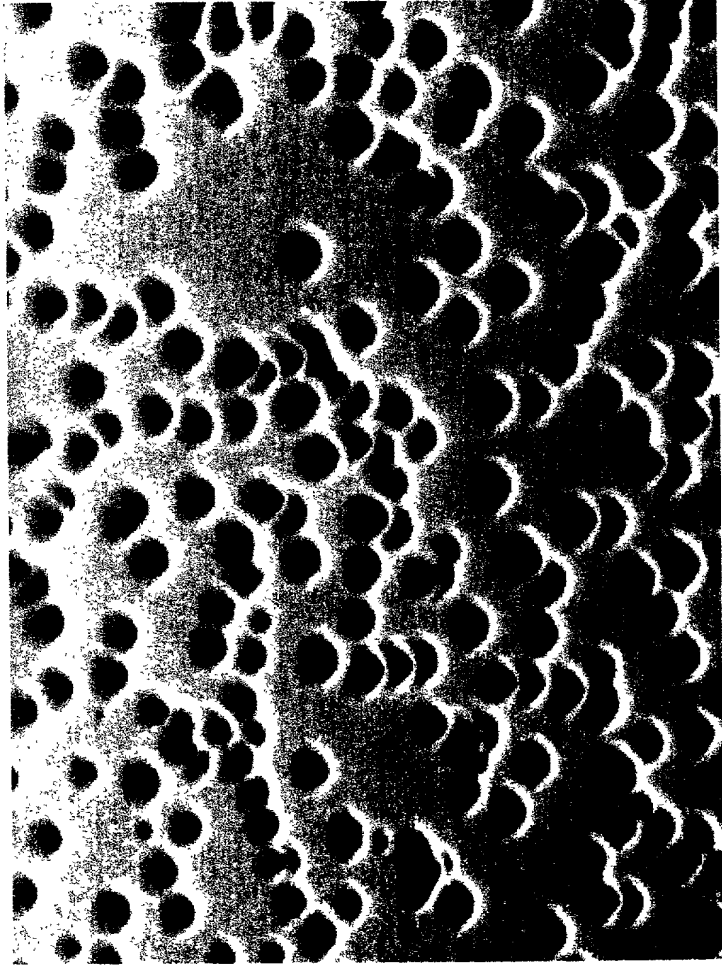
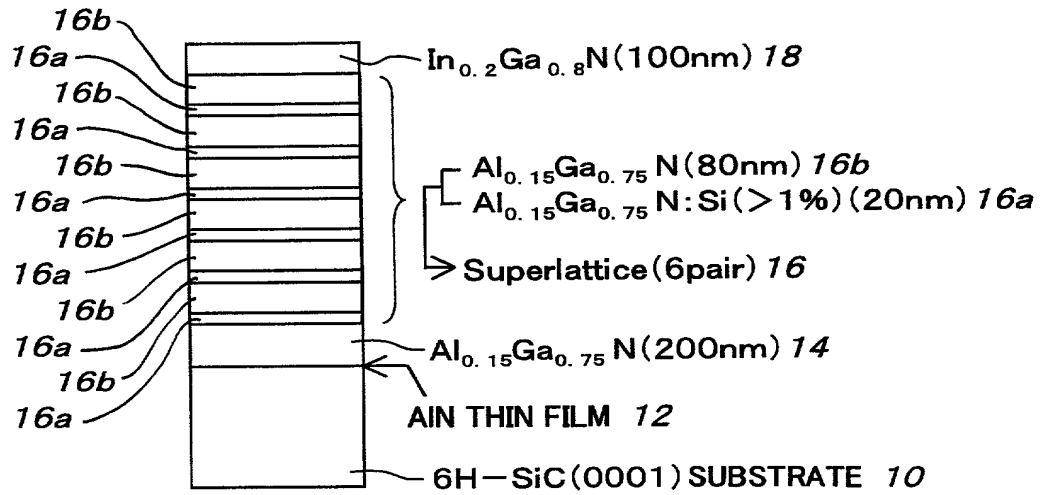


FIG. 2



0.5 μm

FIG. 3



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FIG. 4

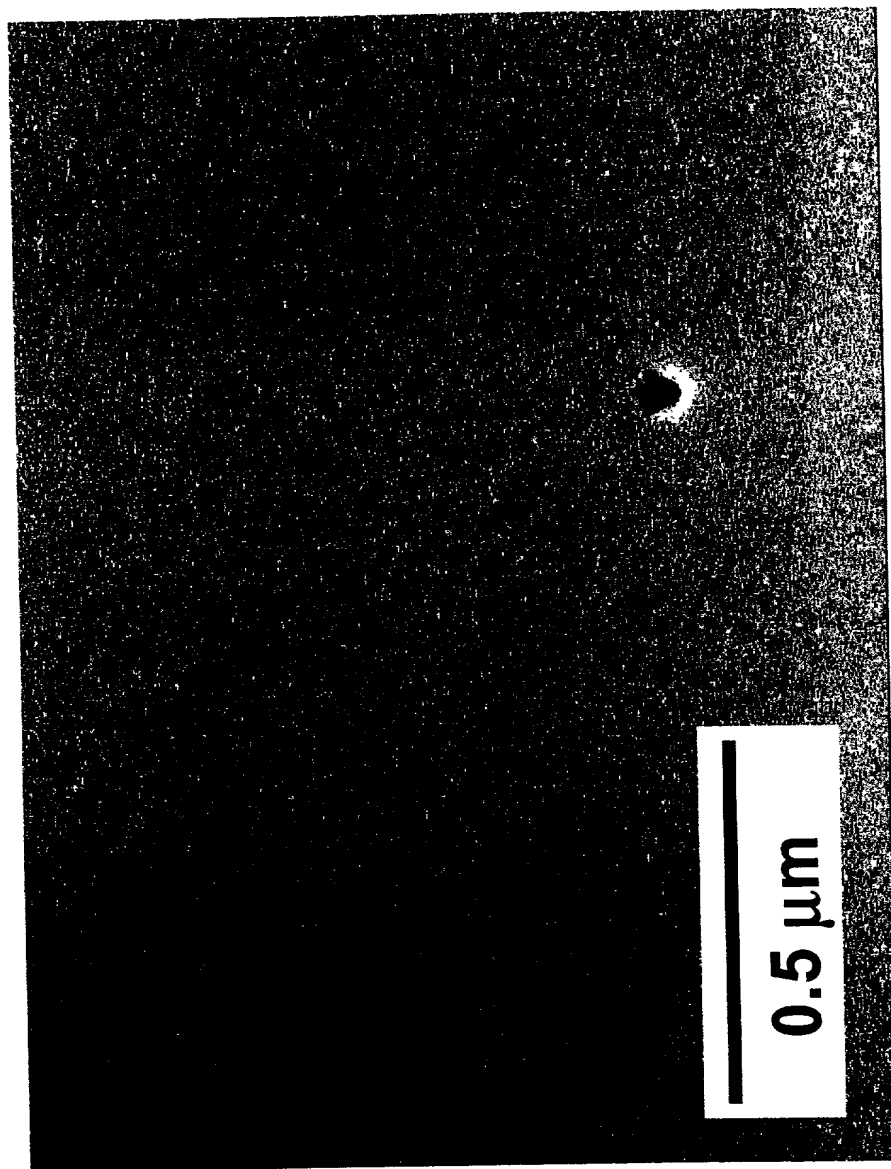
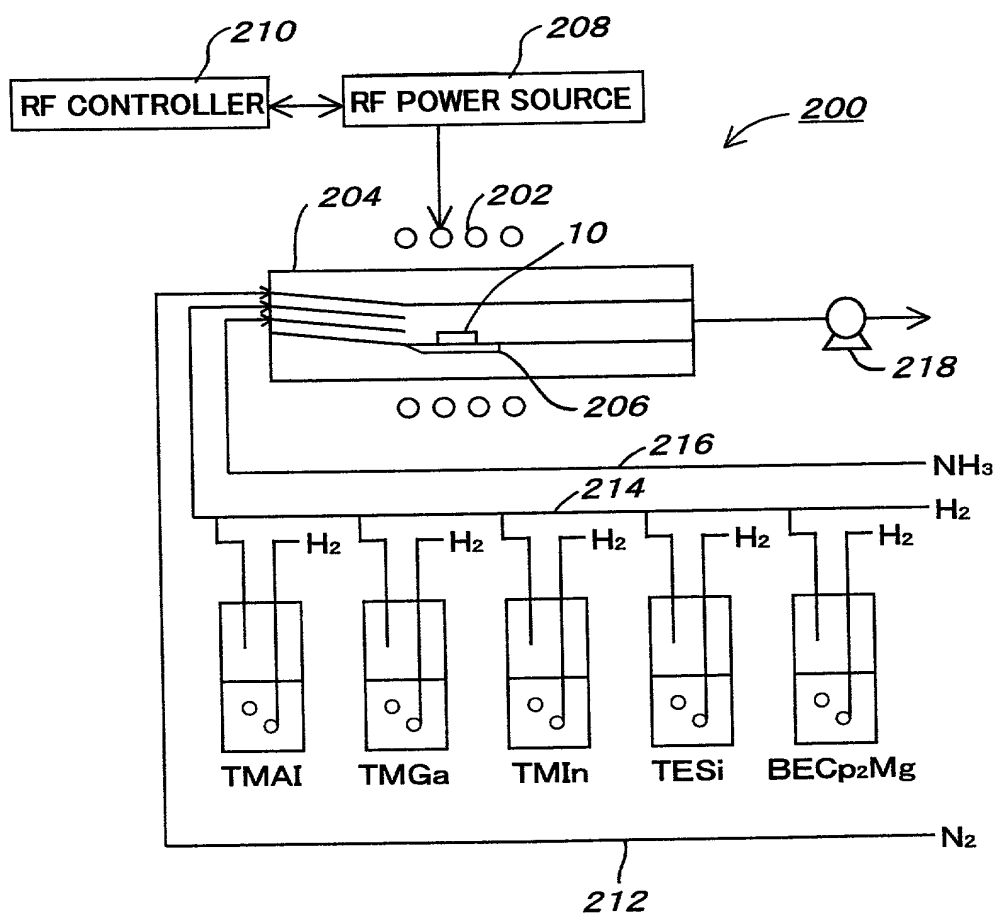


FIG. 5



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TIMING CHART FOR INTRODUCING MATERIAL GASES

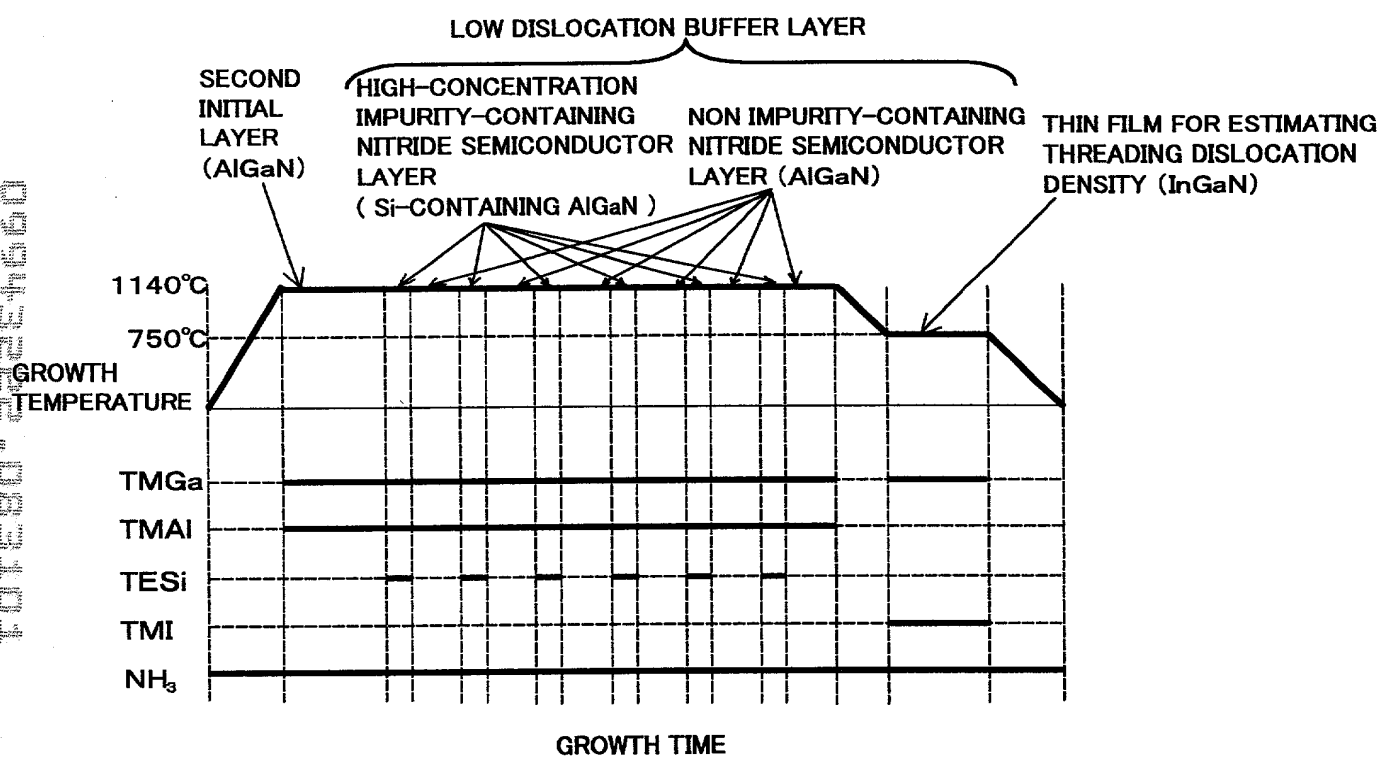


FIG. 7

RELATIONSHIP BETWEEN TESI FLOW RATE
AND THREADING DISLOCATION DENSITY

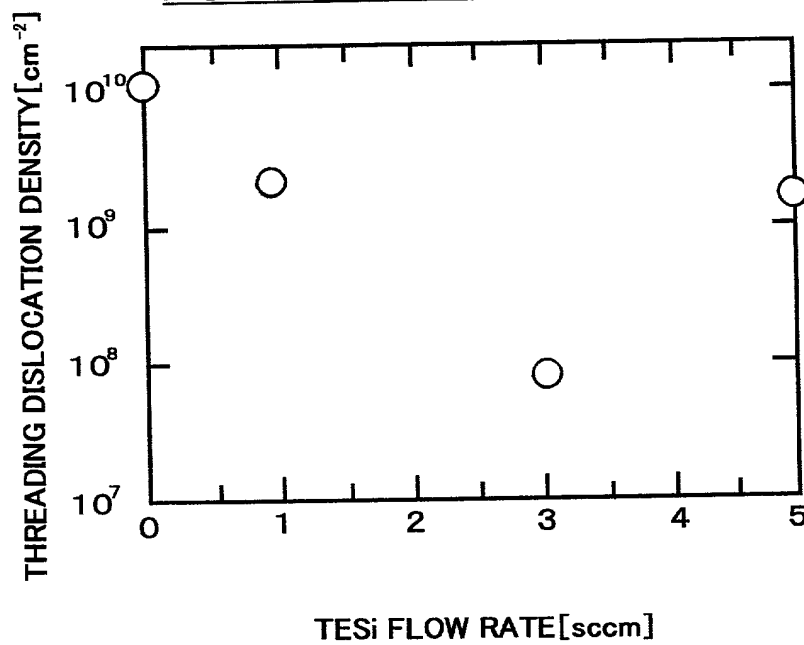
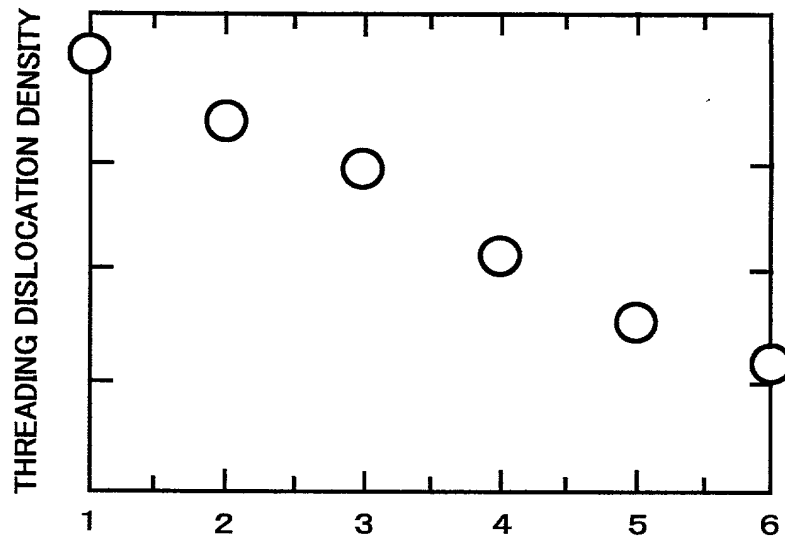


FIG. 8

RELATIONSHIP BETWEEN PERIOD OF
SUPERLATTICE BUFFER LAYER AND
THREADING DISLOCATION DENSITY



PERIODICITY OF SUPERLATTICE BUFFER LAYER (NUMBER OF TIMES)

TOP-22E4660

FIG. 9

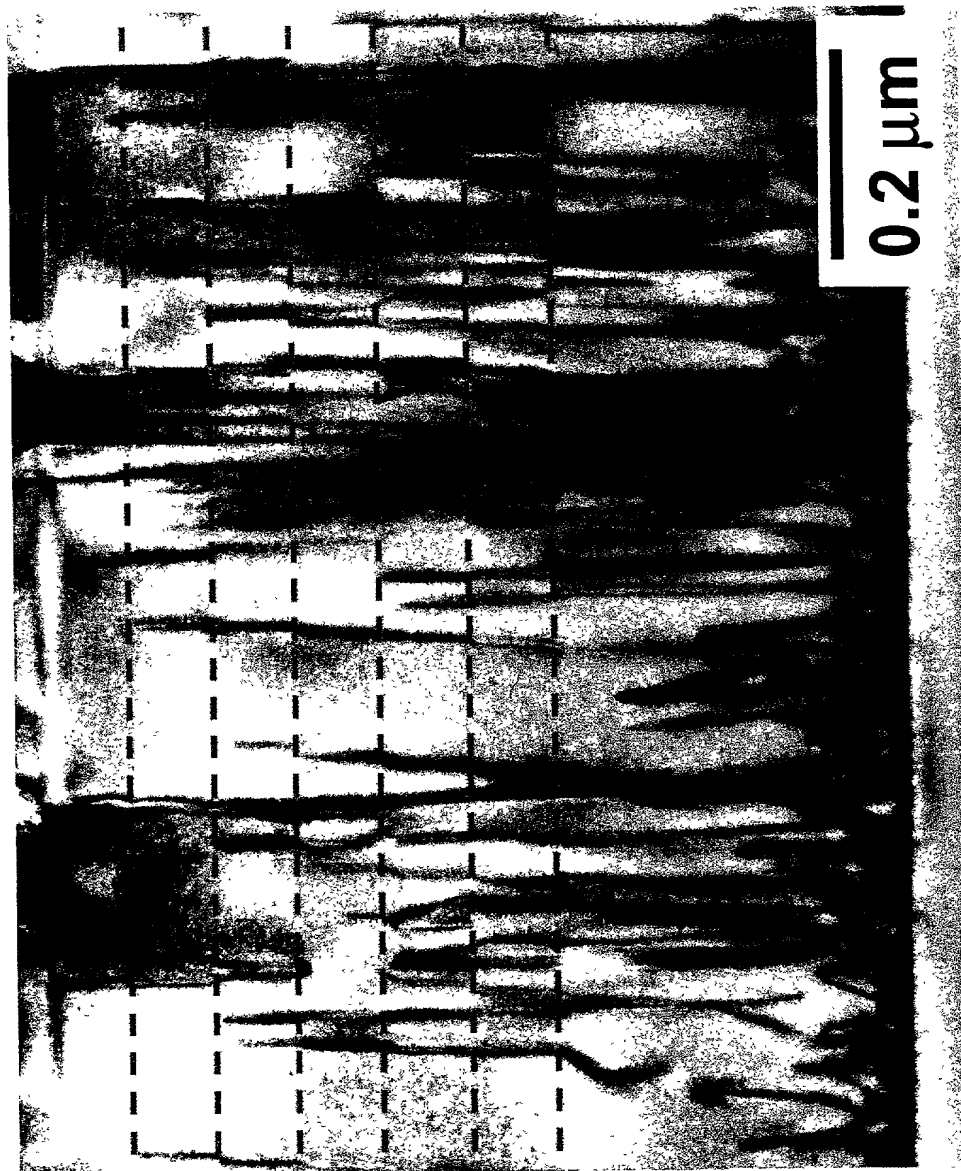


FIG. 10

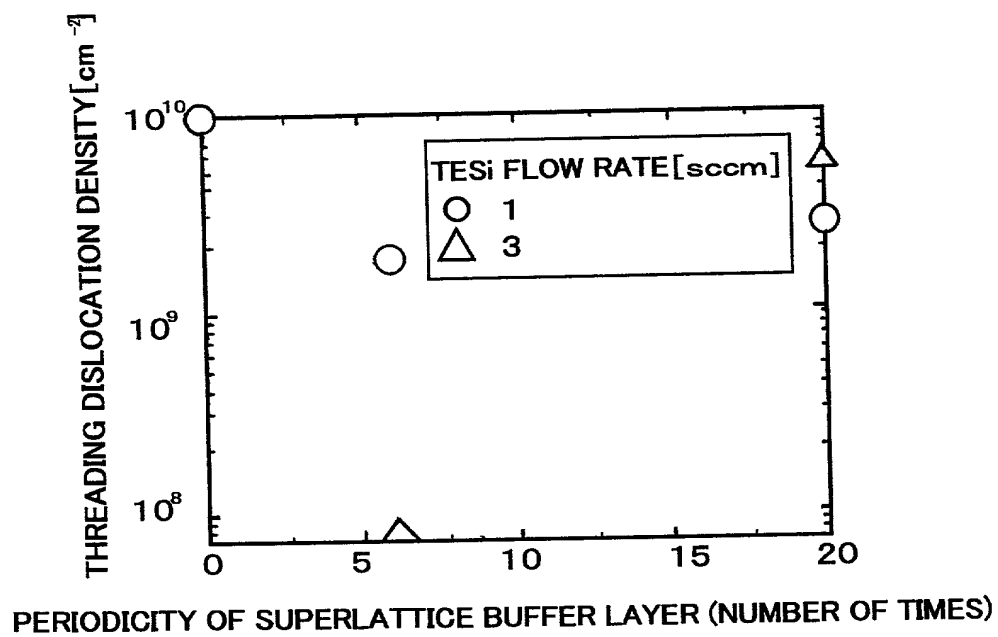


FIG. 11

NITRIDE SEMICONDUCTOR HFET
(Heterostructure Field Effect Transistor)
(EXAMPLE, AlGaN/GaN-HFET)

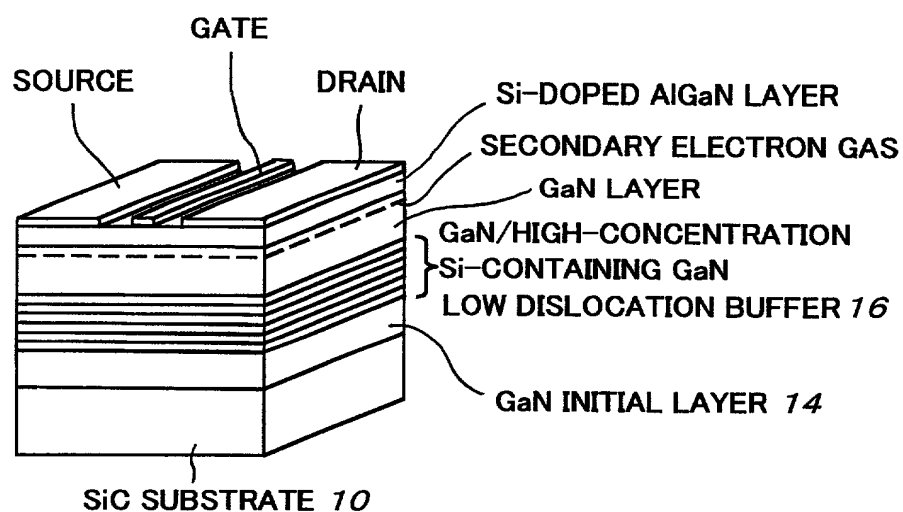


FIG. 12

NITRIDE SEMICONDUCTOR LASER DIODE (EXAMPLE, InGaN LASER)

